

TO-92L Plastic-Encapsulate Transistors

KTA1241 TRANSISTOR (PNP)

FEATURES

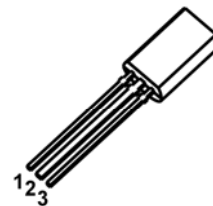
- Low Collector Saturation Voltage
- High Power Dissipation

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current	-5	A
P_C	Collector Power Dissipation	0.9	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	139	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

TO - 92L

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-8			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-8\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	100		320	
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-4\text{A}$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-3\text{A}, I_B=-75\text{mA}$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2\text{V}, I_C=-4\text{A}$			-1.5	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		62		pF
Transition frequency	f_T	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$		170		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y
RANGE	100-200	160-320